Current Transducers HAS 50 to 600-S

For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit).





Electrical data

Primary nomin r.m.s. current I _{PN} (A)	al Primary current measuring range I _P (A)	Туре		
50 100 200 300 400 500 600		HAS 50-S HAS 100-S HAS 200-S HAS 300-S HAS 400-S HAS 500-S HAS 600-S		
$\begin{array}{c} \mathbf{V}_{c} \\ \mathbf{I}_{c} \\ \mathbf{I}_{oc} \\ \mathbf{V}_{d} \\ \mathbf{V}_{b} \\ \mathbf{R}_{ls} \\ \mathbf{V}_{OUT} \\ 40 \\ \mathbf{R}_{OUT} \\ \mathbf{R}_{L} \end{array}$	Supply voltage (± 5 %) Current consumption Overload capacity R.m.s. voltage for AC isolar R.m.s. rated voltage, safe s Isolation resistance @ 500 Output voltage @ $\pm I_{PN}$, $R_{L} =$ Output internal resistance Load resistance	separation VDC	± 15 ± 15 30,000 3 500 ¹⁾ > 1000 100 > 1	V mA kV kV ν MΩ ± 4V ± Ω kΩ

Accuracy - Dynamic performance data

-, -,			
Accuracy @ I_{PN} , $T_{A} = 25^{\circ}C$ (without offset)	<±1	%
Linearity ²⁾ $(0 \dots \pm \hat{I}_{PN})$		<±1	% of $I_{_{\rm PN}}$
Electrical offset voltage, $T_{A} = 25^{\circ}C$		< ± 20	mV
Hysteresis offset voltage $\hat{\mathbf{Q}} \mathbf{I}_{p} = 0;$			
after an excursion of 1 x I		< ± 20	mV
	HAS 50-S	<±2	mV/K
ŬL.	HAS 100 to HAS 600-S	< ± 1	mV/K
Thermal drift of the gain (% of reading)		< ± 0.1	%/K
Response time @ 90% of	I _D	< 3	μs
di/dt accurately followed		> 50	Aμs
Frequency bandwidth (- 3 c	dΒ) ³⁾	DC 50) kHz
l data			
Ambient operating tempera	ature	- 10 +	80 °C
, e 1		- 25 +	80 °C
Mass		. 60	g
Standards ⁴⁾		EN 501	
	Accuracy ($ \mathbf{I}_{PN}, \mathbf{T}_{A} = 25^{\circ}C ($ Linearity ²⁾ (0± \mathbf{I}_{PN}) Electrical offset voltage, \mathbf{T}_{A} Hysteresis offset voltage ($ \mathbf{G} $ after an excursion of 1 x \mathbf{I}_{PN} Thermal drift of \mathbf{V}_{OE} Thermal drift of the gain (% Response time ($ \mathbf{G} $ 90% of di/dt accurately followed Frequency bandwidth (- 3 of I data Ambient operating temperation Ambient storage temperation Mass	Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}$ C Hysteresis offset voltage $\mathbf{Q} \ \mathbf{I}_{p} = 0$; after an excursion of 1 x \mathbf{I}_{pN} Thermal drift of \mathbf{V}_{OE} HAS 50-S HAS 100 to HAS 600-S Thermal drift of the gain (% of reading) Response time @ 90% of \mathbf{I}_{p} di/dt accurately followed Frequency bandwidth (- 3 dB) ³ I data Ambient operating temperature Ambient storage temperature Mass approx	Accuracy @ I_{PN} , $T_A = 25^{\circ}C$ (without offset)< ± 1

 $I_{PN} = 50..600 \text{ A}$ $V_{OUT} = \pm 4 \text{ V}$



Features

- Hall effect measuring principle
- Galvanic isolation between primary and secondary circuit
- Isolation voltage 3000 V~
- Low power consumption
- Extended measuring range $(3 \times I_{_{PN}})$
- Insulated plastic case made of polycarbonate PBT recognized according to UL 94-V0

Advantages

- Easy mounting
- Small size and space saving
- Only one design for wide current ratings range
- High immunity to external interference.

Applications

- AC variable speed drives
- Static converters for DC motor drives
- Battery supplied applications
- Uninterruptible Power Supplies (UPS)
- Switched Mode Power Supplies (SMPS)
- Power supplies for welding applications.

Notes : ¹⁾ Pollution class 2, overvoltage category III.

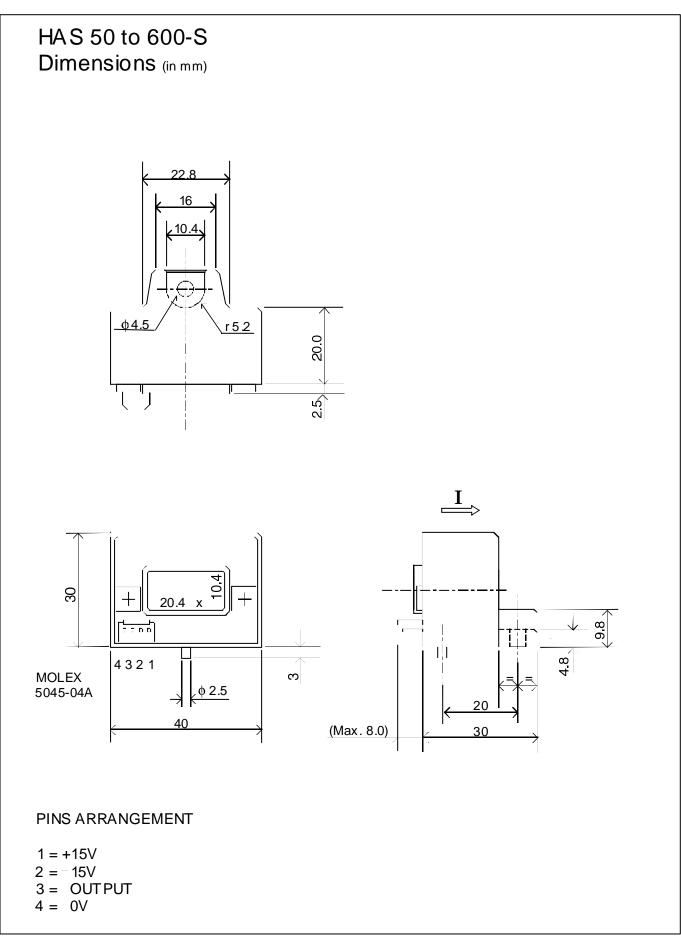
- ²⁾ Linearity data exclude the electrical offset.
- ³⁾ Please refer to derating curves in the technical file to avoid excessive core heating at high frequency.

⁴⁾ Please consult characterisation report for more technical details and application advice.

LEM Components

981007/4





LEM reserves the right to change limits and dimensions.

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Datasheets for electronics components.